

to claim 23, wherein said field effect transistor is a partial depletion-type field effect transistor. --

REMARKS

Reconsideration and allowance of this application, as amended, is respectfully requested.

This amendment is in response to the restriction requirement dated September 6, 2002.

In response to the election of species requirement set forth in the Office Action, applicants hereby elect Species 1 directed to a method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer, noting that claims 12, 13, 17 and 18 are readable thereon, as indicated in the Office Action. With regard to this, minor amendments have been made to claims 12 and 13 to correct grammatical and spelling informalities noted therein. In addition, new claims 19-23 have been added for consideration. With regard to this, it is noted that new independent claim 23 is a generic claim which covers the subject matter of claims 12, 13 and 17-22. Regarding this, new claim 19 is similar to claim 17, and, as such, falls within the elected species 1. New claims 20-22 contain subject matter similar to that of the non-elected species. However, by virtue of inclusion of new generic claim 23, it is respectfully submitted that claim 23 links the claims 19-22. As such, examination of all of claims 19-23 is also respectfully requested.

In addition, by the present amendment, new claims 24-30 have been added. These dependent claims specify that the field effect transistor utilized in the method of the parent claims is a partial depletion type field effect transistor, as illustrated in Fig. 2 and described in the specification on page 11, lines 19 and 20 and on page

14, line 18 et seq. Entry and examination of these dependent claims, together with their respective independent parent claims is respectfully requested.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with markings to show changes made."

If the Examiner believes that there are any other points which may be clarified or otherwise disposed of, either by telephone discussion or by personal interview, the Examiner is invited to contact applicants' undersigned attorney at the number indicated below.

To the extent necessary, the applicants petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the deposit account of Antonelli, Terry, Stout & Kraus, Deposit Account No. 01-2135 (501.38435VX1).

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP

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VERSION WITH MARKINGS TO SHOW CHANGES MADEIn the Claims:

Claims 12 and 13 have been amended as follows:

12. (Amended) A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel forming region of said [filed] field effect transistor, comprising [the following step of]:

applying a potential lying in a direction to induce an electrical charge of conduction type opposite to a channel formed in a surface layer of the channel forming region of said field effect transistor, in a lower portion of the channel forming region thereof to said body electrode and said back gate electrode or at least said back gate electrode so as to increase a threshold voltage of said field effect transistor.

13. (Amended) A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel forming region of said [filed] field effect transistor, comprising [the following step of]:

applying a potential lying in a direction to induce an electrical charge of conduction type opposite to a channel formed in a surface layer of the channel

forming region of said field effect transistor, in a lower portion of the channel forming region thereof to said body electrode and said back gate electrode or at least said back gate electrode so as to stabilize a threshold voltage of said field effect transistor and increase a withstand voltage of the drain thereof.

New claims 19-30 have been added.